



EUVL for HVM: Progress Update

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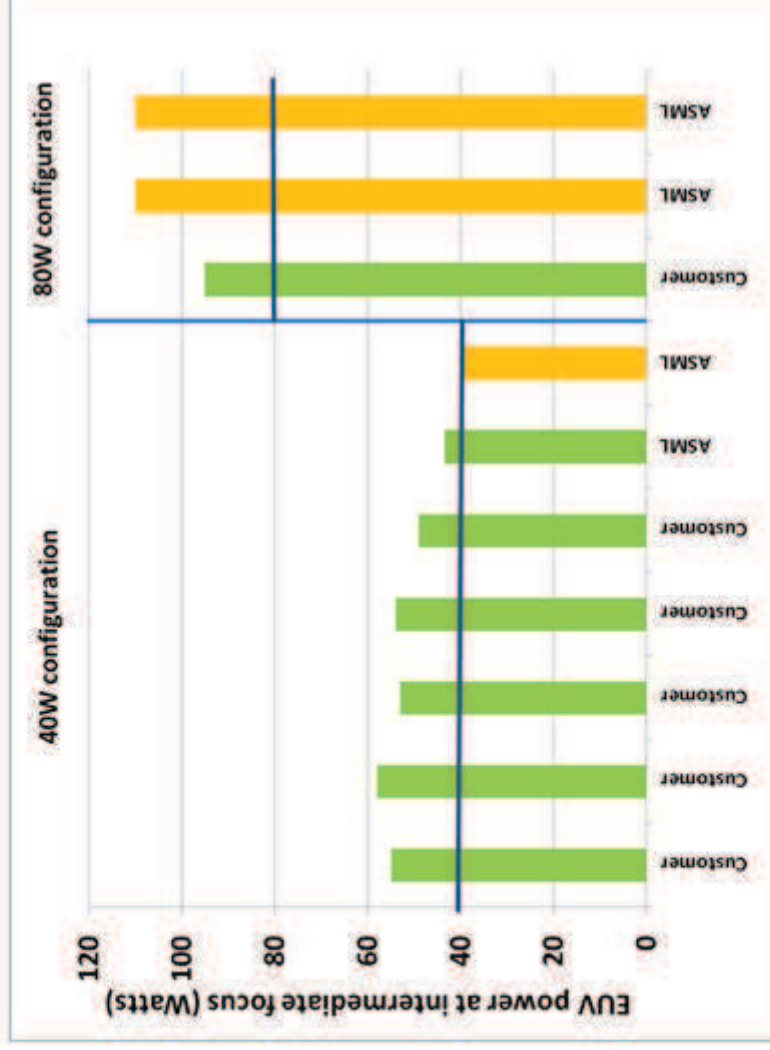
Outline

- EUV source and system performance
- EUV/193i complementary patterning
- EUV infrastructure

Worldwide fleet 40-80W

Multiple systems capable of >90W

All systems demonstrated capability to meet performance target



All results normalized to clean collector conditions

ASML

public
Slide 1



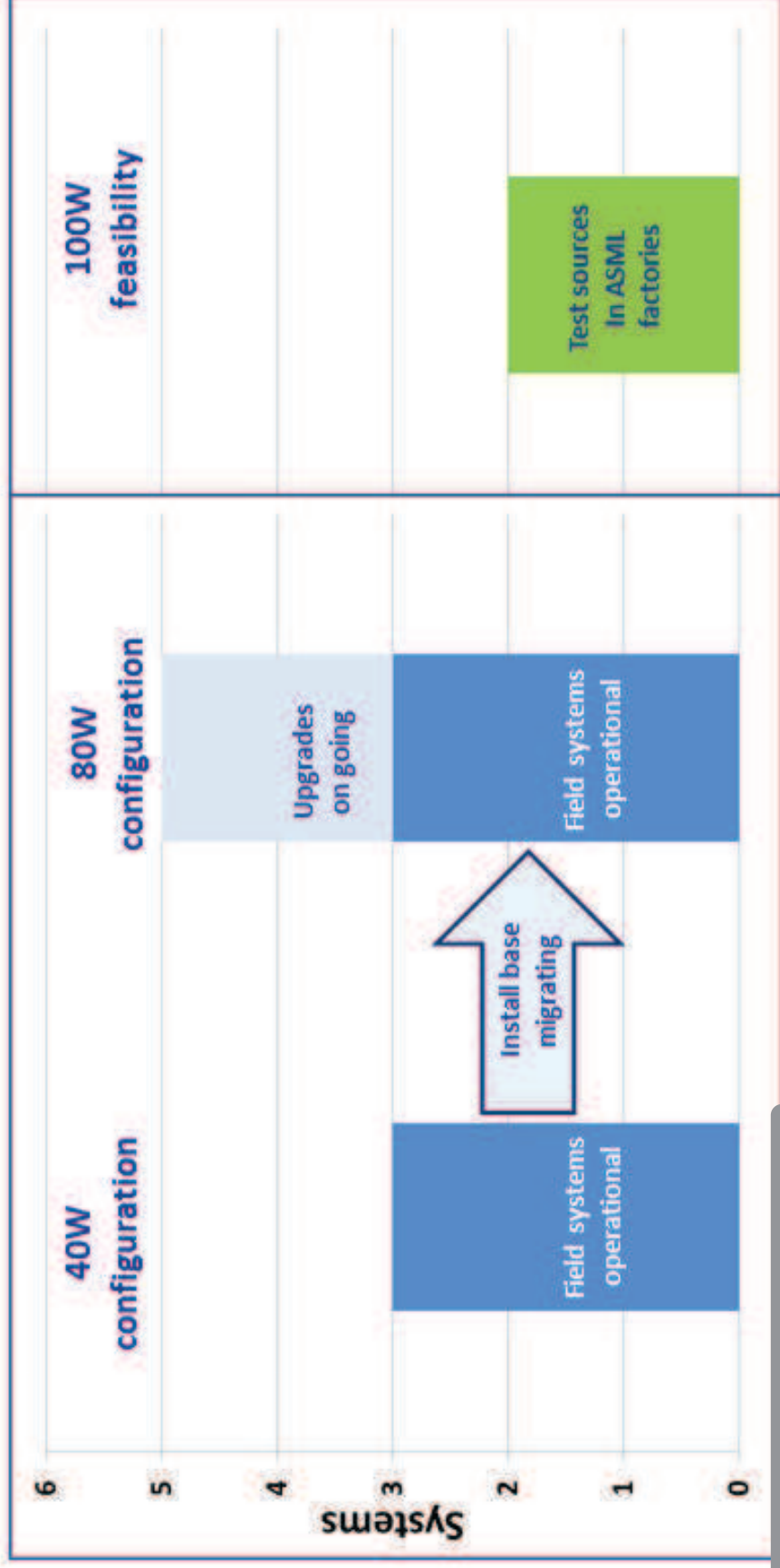
Slide courtesy ASML

Install base quickly migrating to 80W config

NXE:3300B install base migrating from 40W to 80W configuration
Upgrade enables 2x improvement in power, ~10% availability gain

ASML

Public



Slide courtesy ASML.

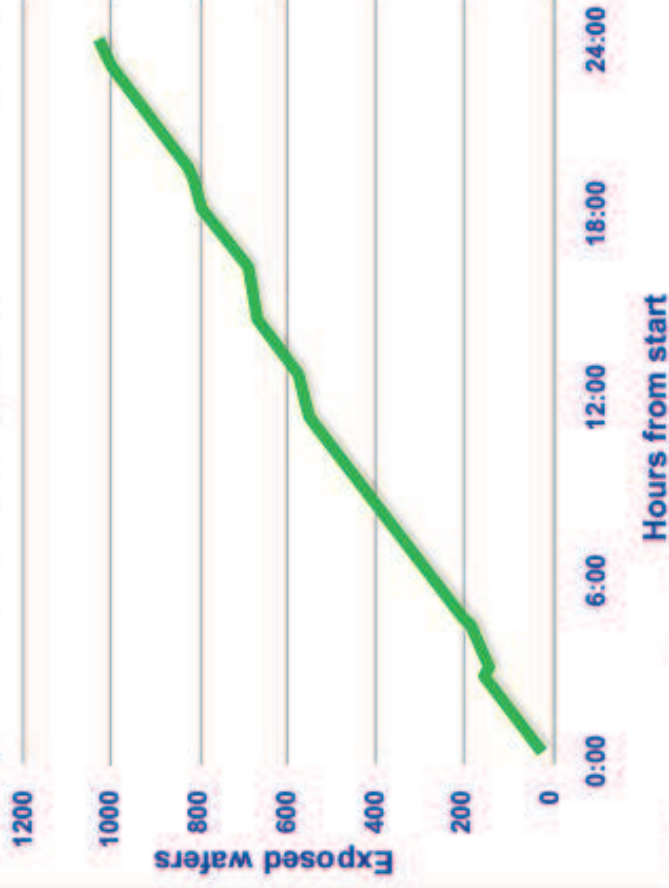
Short-term productivity >1000wpd

Today: 1,000 wafers per day capability demonstrated
On a field system, using customer exposure conditions, on 2 different days

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Slide 5
February 2015

1,022 wafers exposed in 24 hours



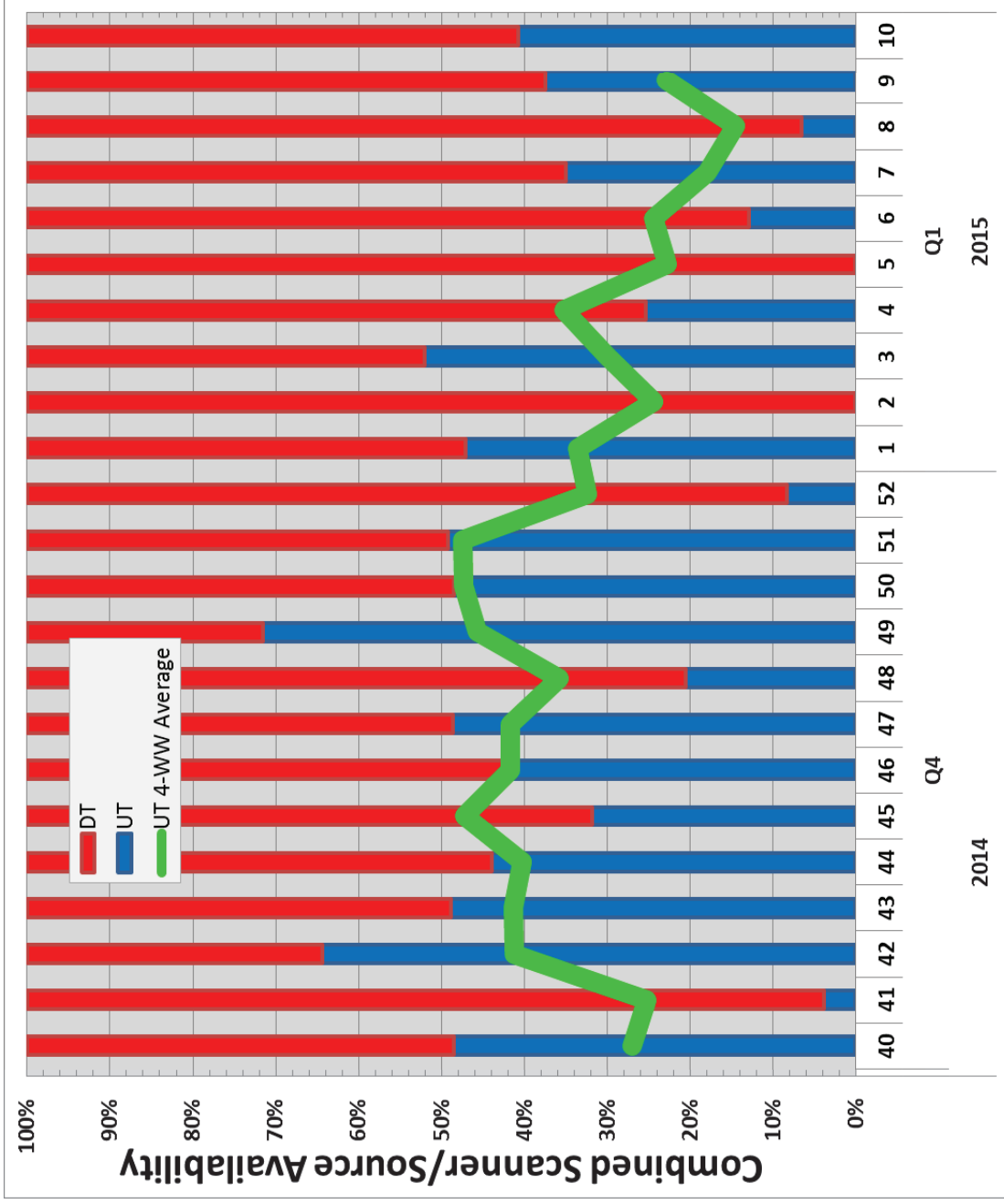
80W source configuration

970 wafers exposed in 24 hours



Alberto Pirati, SPIE Advanced Lithography, 2015

However...



Availability and predictability are still poor

Extended demo of availability and predictability

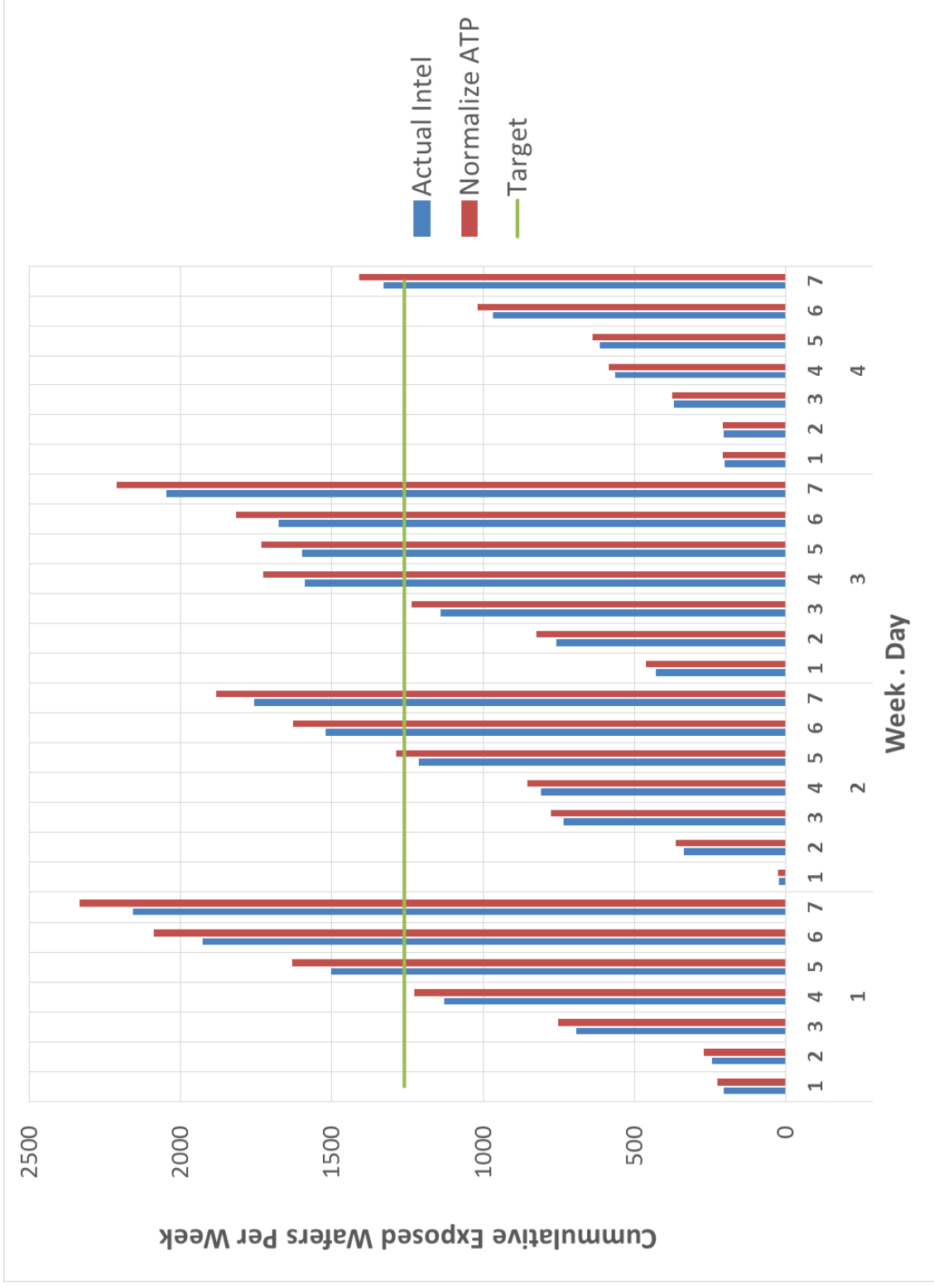
- 21hrs/day wafer cycling with mix of test-chip wafers (CDs, overlay, in-line defects, e-test) and bare silicon
- 3-hr daily Intel engineering window (no tool work)
- Availability counted 24hrs/day. Wafer output targets set for 21hrs/day in 40W config.
- Only good wafers (meeting dose control specs) counted
- Goal: demonstrate tool can run as advertised for 40W config today, *including imaging and overlay*

Targets and results from 4-week demo

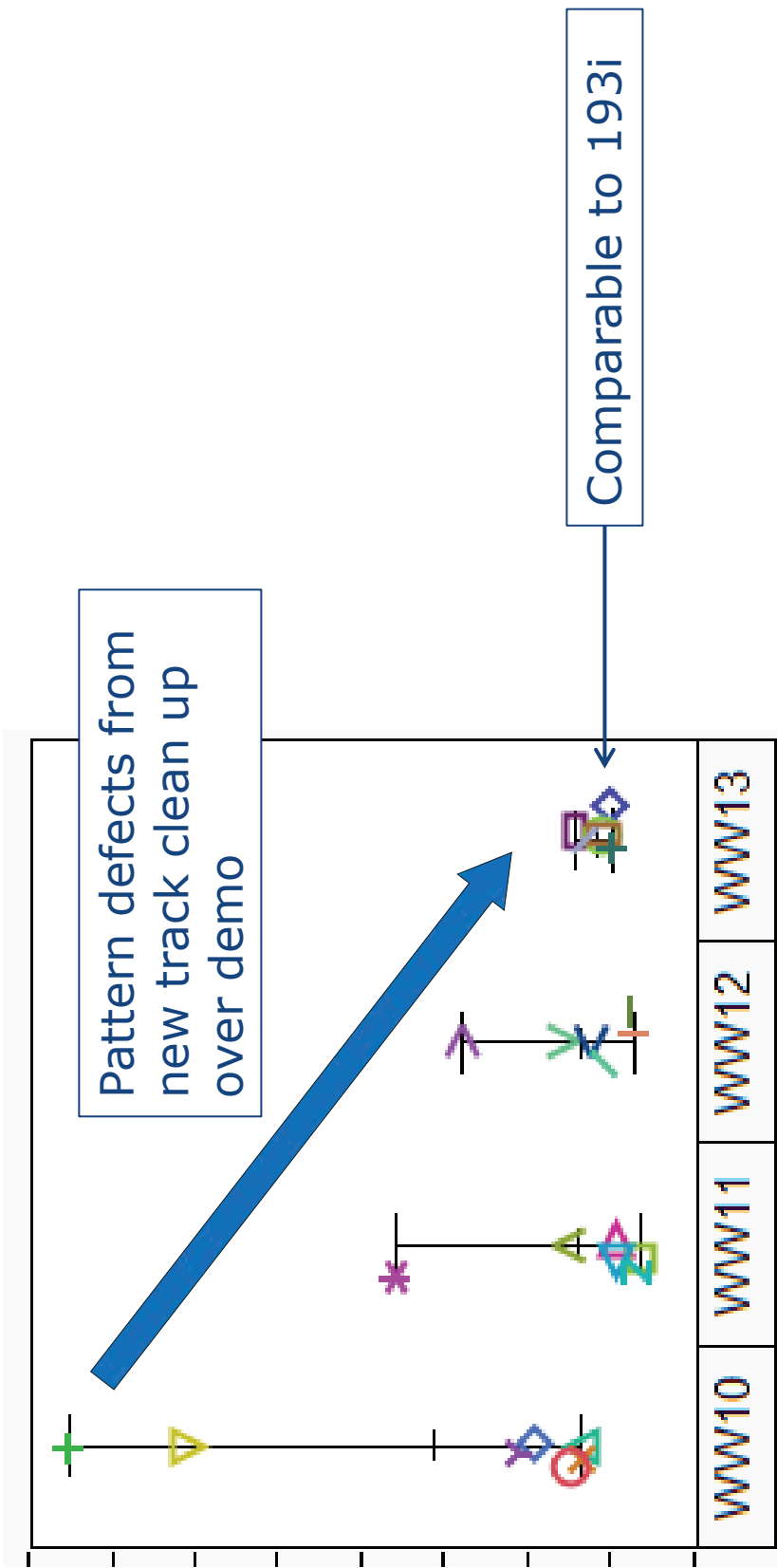
	Nominal Target	Demo-Time Adjusted Target	Result
Availability (scanner + source)	46%	46%	61%
TPT - good wafers per day	180	170	<ul style="list-style-type: none"> • 280 normalized WPD • 260 actual exposed WPD (raw count)
TPT - good wafers per week	1260	1189	<ul style="list-style-type: none"> • 1959 normalized WPD • 1822 actual exposed WPD (raw count)
No consecutive DT > 72hrs	<72hrs	<72hrs	Max consecutive downtime = 36hrs (DG swap + Sn catch drain + RF generator failure/replacement on PA0)

- Goal: demonstrate tool can run as advertised for 40W config today
- Targets based on 125 fields/wafer at 15mJ/cm² dose
- Actual wafers exposed were a variety of shot maps and doses, so “normalized” count converts to equivalent at 125 fields/15mJ
- Integrated test-chip wafers allowed verification of imaging, overlay, and defects throughout demo → results all good

Demo cumulative wafers per week



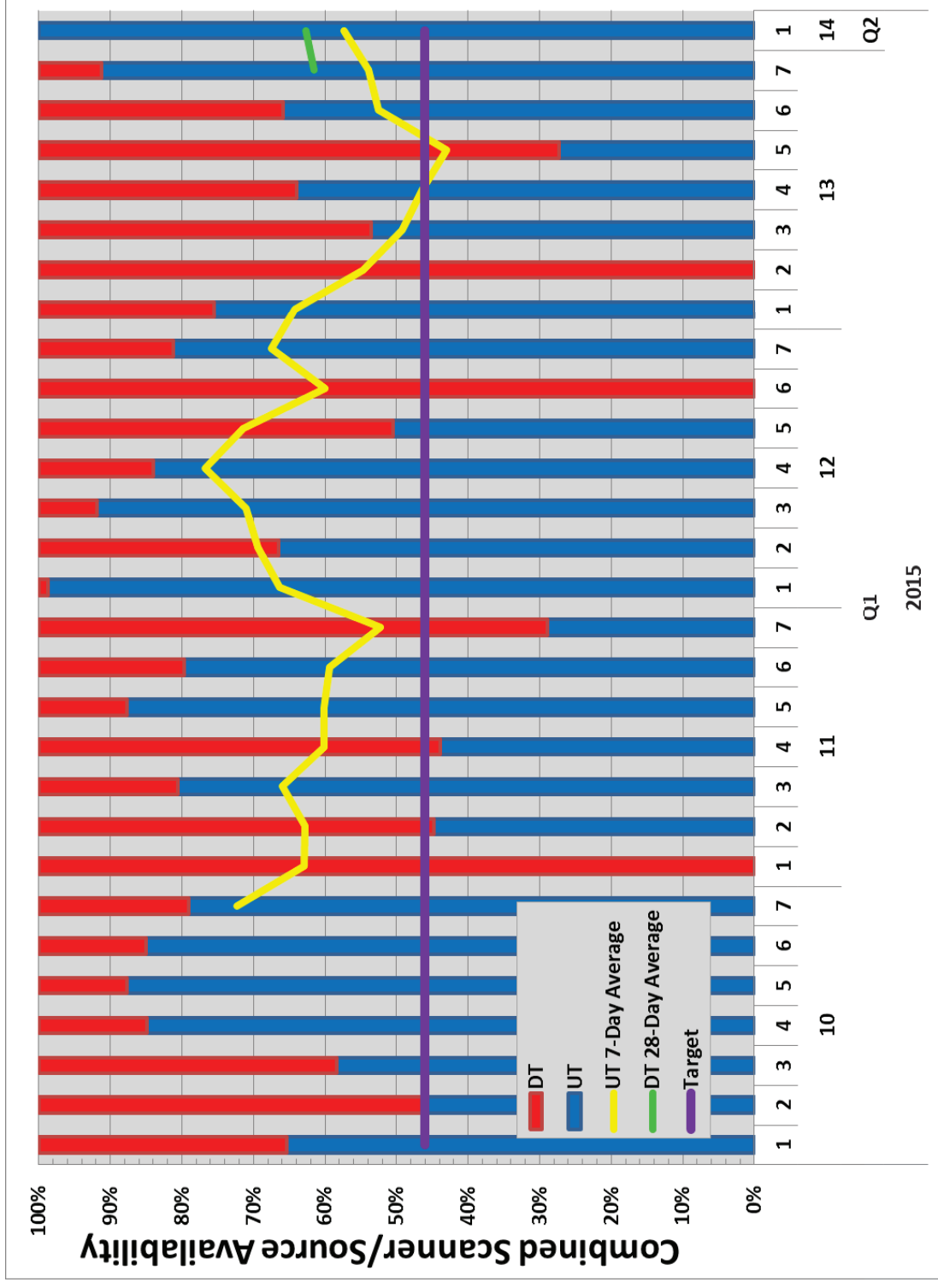
Demo in-line defect trend



- Track cleans up over time. Scanner contribution is OK.



Demo availability (4 weeks)



- Far from OK for production, but better than expected for current 40W config

Over longer term, availability is unstable



Summary of EUVL status

- Two years of solid progress on EUVL
 - Eight 0.33NA systems shipped, generally meeting all performance specs not related to source power
 - 80W config proliferating quickly, and 100W (@IF) MOPA/PP demonstrated in the field
 - ~500wpd, then ~1000wpd in short-term (1-2 day) demonstrations
 - 4 week demonstration of availability and output consistent with 40W tool configuration, and stable imaging and overlay performance
- Introduction in production is a question of “when” rather than “if”
 - Availability, stability and operating cost are still concerns
 - Need to ensure infrastructure does not gate HVM